

FIGURE 1(a)

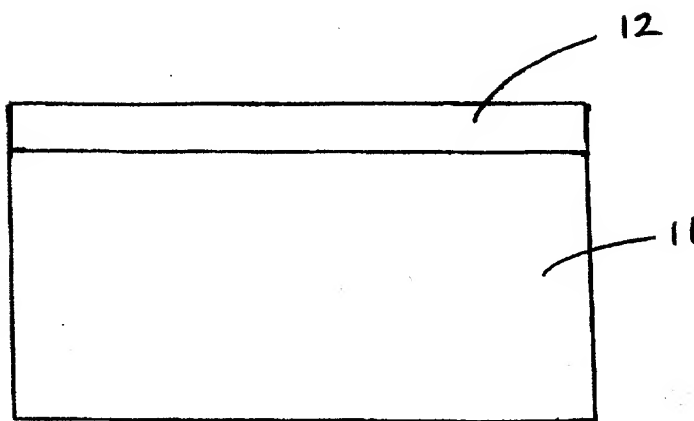


FIGURE 1(b)

202502280001

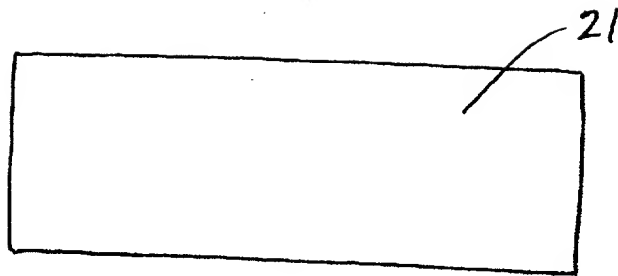


FIGURE 2(a)

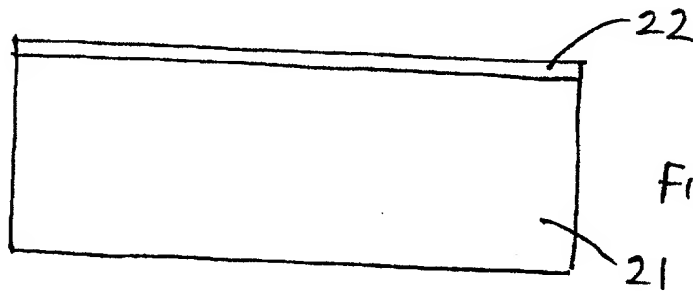


FIGURE 2(b)

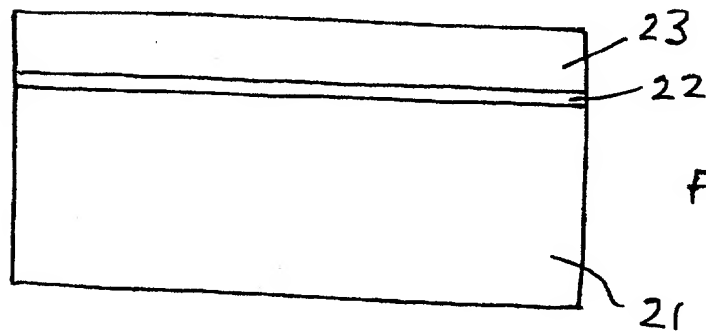


FIGURE 2(c)

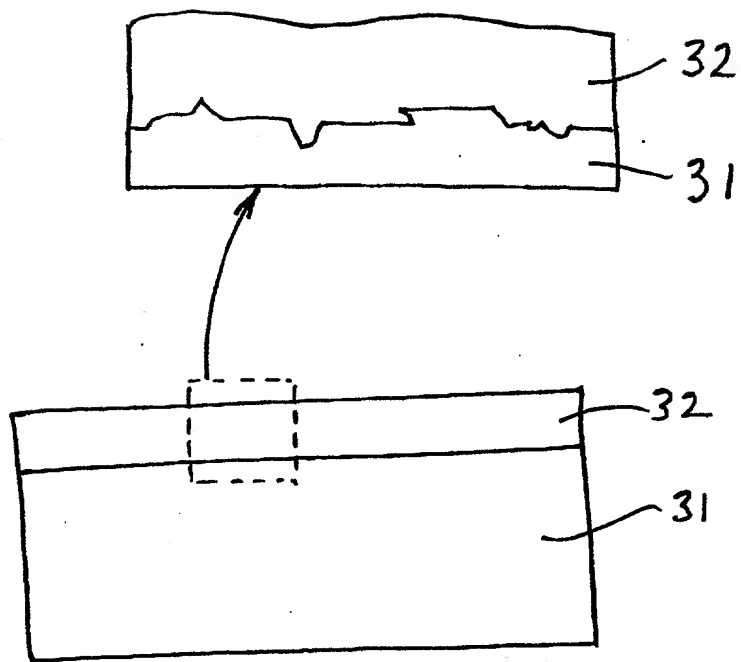


FIGURE 3

20240507 14:55:26

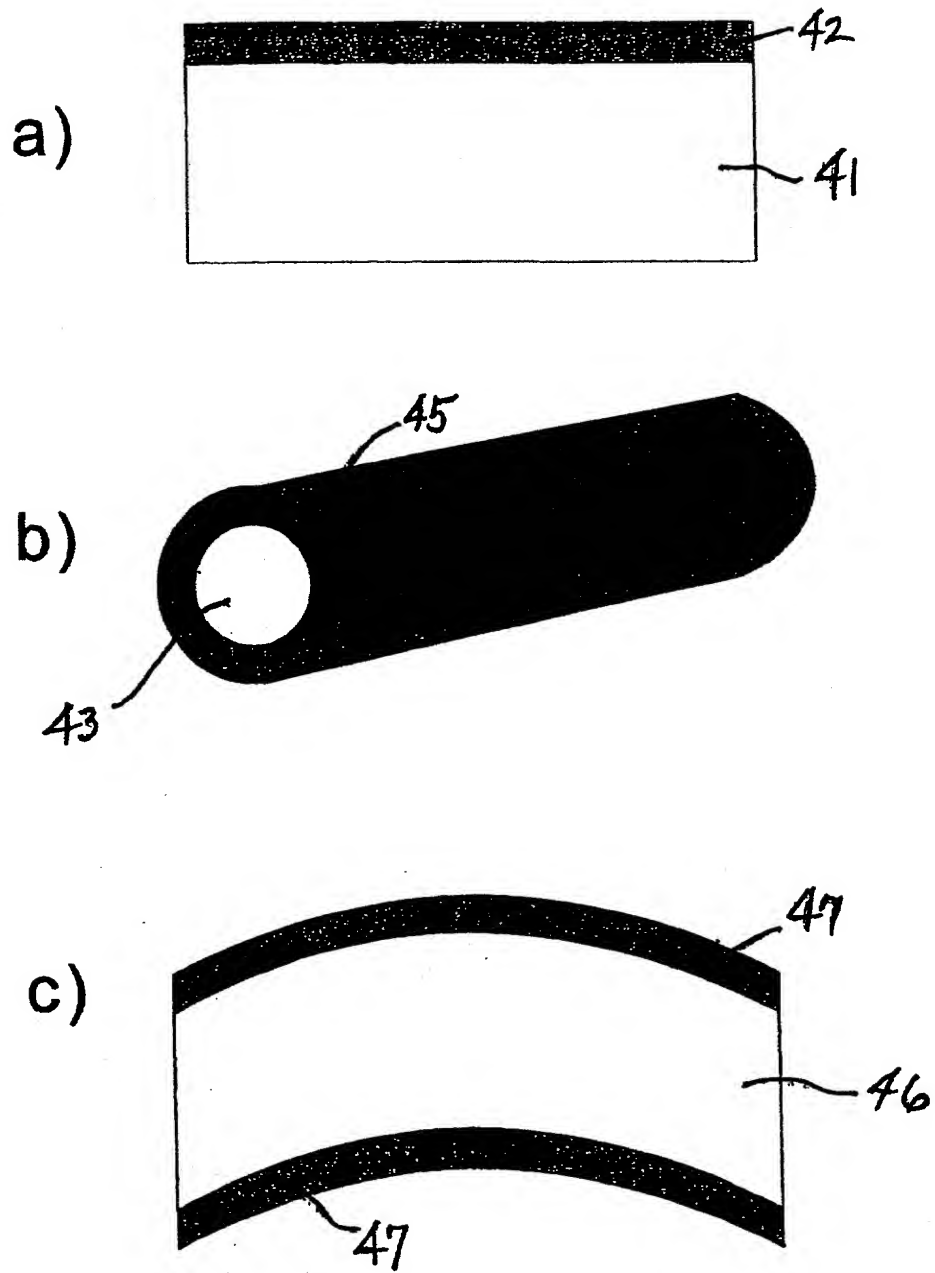
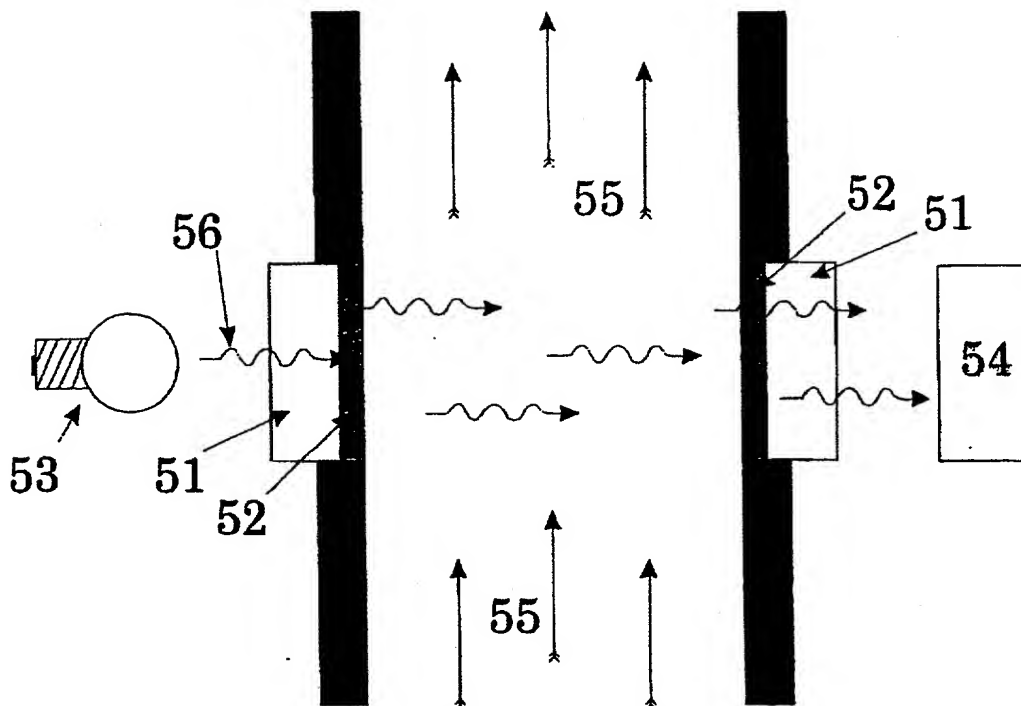
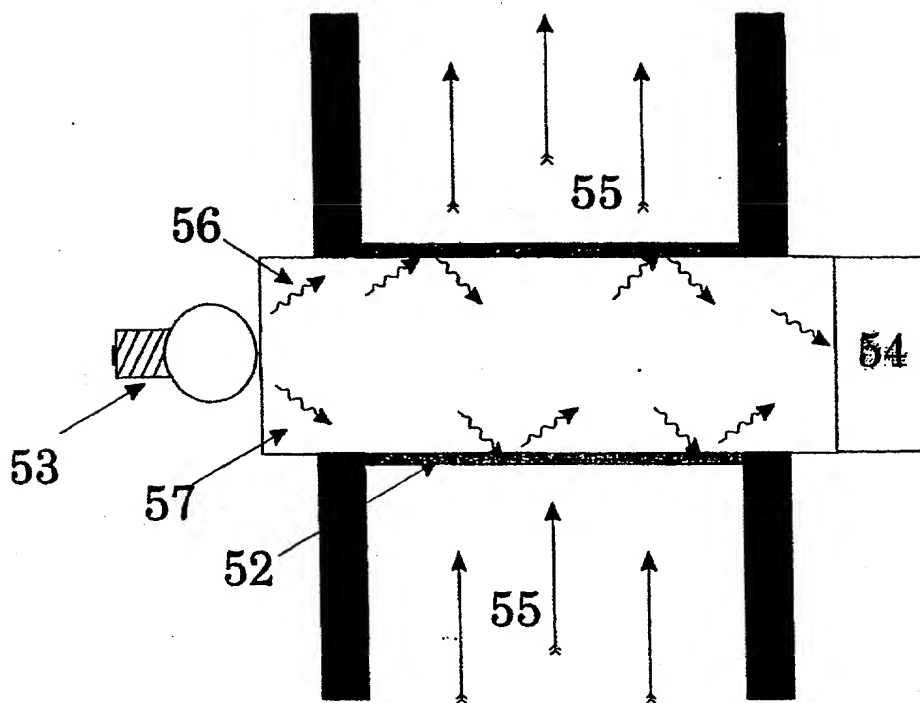


FIGURE FOUR.

a)



b)



A cross-sectional view of a semiconductor device. A central channel (112) is formed in a substrate (110). The channel is bounded by side walls (113). On the top surface of the side walls, there are contact regions (114) and a central gate region (115). The device is shown in a cross-section with a central channel and side contacts.

Figure 6